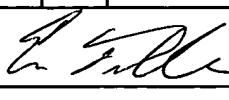
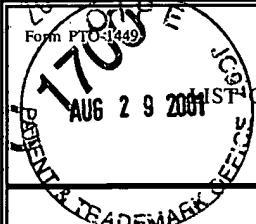
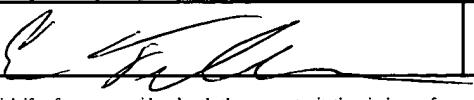


07/13/01

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1724	SERIAL NO. Unknown		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Cem Basceri et al.			
					FILING DATE Filed Herewith	GROUP Unknown		
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
EF	AA			Cem Basceri et al. (as filed)				Filed Concurrently
EF	AB	09/476,516		Cem Basceri (as filed and as amended)				01/03/00
EF	AC	09/580,733		Cem Basceri (as filed)				05/26/00
EF	AD	5,459,635	10/17/95	Tomozawa et al.		361	321.5	
EF	AE	5,618,761	04/08/97	Eguchi et al.		438	785	
	AF							
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country		Class	Subclass	Translation
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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EXAMINER				DATE CONSIDERED		12/06/01		
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

 Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1724	SERIAL NO. 09/005,286	
		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT Cem Basceri et al.		
					FILING DATE July 13, 2001		GROUP Unknown
		U.S. PATENT DOCUMENTS					
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA	5,256,455	10/26/93	Numasawa			
EF	AB	5,731,948	01/21/97	Endo			
EF	AC	5,776,254	03/24/98	Yializis et al.			
EF	AD	5,783,253	07/07/98	Yuuki et al.			
EF	AE	5,798,903	07/21/98	Roh			
EF	AF	6,043,526	08/25/98	Dhote et al.			
EF	AG	6,046,345	03/28/00	Ochiai			
EF	AH	6,078,492	04/04/00	Kadokura et al.			
EF	AI	6,153,898	06/20/00	Huang et al.			
EF	AJ	6,037,205	11/28/00	Watanabe			
EF	AK	6,037,205	03/14/00	Huh et al.			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes
EF	AL	0 855 735 A2	26.01.98	EPO - Zhao et al.; Applied Materials, Inc.			
EF	AM	0 957 522 A2	12.05.99	EPO - Ueda, Michihito; Matsushita Electric Ind. Co.,			
EF	AN	WO 98/39497	20.02.98	WIPO - Simpson, John et al.			
EF	AO	0 474 140 A1	30.08.91	EPO - Kamiyama, Satoshi c/o NEC Corporation			
EF	AP	WO 99/64645	11.06.99	WIPO - Narwankar et al.; Applied Materials, Inc;			
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EF	AR	Steve Bilodeau et al., <i>Composition Dependence of the Dielectric Properties of MOCVD Ba<sub>x</sub>Sr<sub>1-x</sub>TiO<sub>3</sub></i> , pp. 1-21 (MRS Fall Meeting 12/01/94).					
EF	AS	Steve M. Bilodeau et al., <i>MOCVD BST for High Density DRAM Applications</i> (Preprint for SEMICON/WEST 07/12/95), 2 pages.					
EF	AT	Y-C Choi et al., Abstract, <i>Improvements of the Properties of Chemical-Vapor-Deposited (Ba<sub>x</sub>Sr)TiO<sub>3</sub> Films Through Use of a Seed Layer</i> , 36 JPN. J. APPL. PHYS. Pt. 1, No. 11, pp. 6824-6828 (1997)					
EXAMINER		DATE CONSIDERED 12/06/01					
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

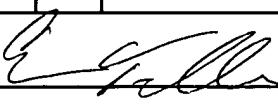
Form PTO-1442 PATENT & TRADEMARK OFFICE AUG 29 2001 L151		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1724		SERIAL NO. 09/905,286		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Cem Basceri et al.				
				FILING DATE July 13, 2001		GROUP Unknown		
U.S. PATENT DOCUMENTS								
*Examiner Initial	Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
EF	AA 5/470,398	11/28/95	Shibuya et al.					
EF	AB 5/254,505	10/19/93	Kamiyama					
EF	AC 6,156,638	12/05/00	Agarwal et al.					
EF	AD 6,165,834	12/26/00	Agarwal et al.					
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FOREIGN PATENT DOCUMENTS								
	Document Number	Date	Country		Class	Subclass	Translation	
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	AN							
	AO							
	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EF	AR	Chung Ming Chu et al., Abstract, <i>Electrical properties and crystal structure of (Ba,Sr)TiO<sub>3</sub> films prepared at low temperatures on a LaNiO<sub>3</sub> electrode by radio-frequency magnetron</i> ..., 70 APPLIED PHYSICS LETTERS No. 2, pp. 249-251 (1997).						
EF	AS	Kazuhiro Eguchi et al., Abstract, <i>Chemical vapor deposition of (Ba,Sr)TiO<sub>3</sub> thin films for application in gigabit scale dynamic random access memories</i> , 14 INTEGRATED FERROELECTRICS Nos. 1-4, Pt. 1, pp. 33-42 (1997).						
EF	AT	Q.X. Jia et al., Abstract, <i>Structural and dielectric properties of Ba<sub>0.3</sub>Sr<sub>0.7</sub> thin films with an epi-RuO<sub>2</sub> bottom electrode</i> , 19 INTEGRATED FERROELECTRICS Nos. 1-4, pp. 111-119 (1998).						
EXAMINER 		DATE CONSIDERED 12/06/01						
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								

Form PTO-1449 <b>OIPE</b> <b>LIST OF ART CITED BY APPLICANT</b> (Use several sheets if necessary) <b>AUG 29 2001</b>				U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1724		SERIAL NO. 09/905,286	
				APPLICANT Cem Basceri et al.					
				FILING DATE July 13, 2001		GROUP Unknown			
<b>U.S. PATENT DOCUMENTS</b>									
*Examiner Initial	Document Number	Date	Name			Class	Subclass	Filing Date If Appropriate	
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<b>FOREIGN PATENT DOCUMENTS</b>									
	Document Number	Date	Country			Class	Subclass	Translation	
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AP									
<b>OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)</b>									
EF	AR		Takaaki Kawahara et al., <i>(Ba, Sr)TiO<sub>3</sub> Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes</i> , 35 JPN. J. APPL. PHYS. Pt. 1, No. 9B, pp. 4880, 4883 (1996).						
EF	AS		<i>Rajesh Khamankar et al., A Novel Low-Temperature Process for High Dielectric Constant BST Thin Films for ULSI DRAM Applications</i> , Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages.						
EF	AT		<i>Yong Tae Kim et al., Abstract, Advantages of RuO<sub>x</sub> bottom electrode in the dielectric and leakage characteristics of (Ba,Sr)TiO<sub>3</sub> capacitor</i> , 35 JPN. J. APPL. PHYS. Pt. 1, No. 12A, pp. 6153-6156 (1996).						
EXAMINER			DATE CONSIDERED						
<i>C. Miller</i>			12/06/01						

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-144 OIPE AUG 29 2001 PATENT DOCUMENTS CITED LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1724		SERIAL NO. 09/905,286	
					APPLICANT Cem Basceri et al.			
					FILING DATE July 13, 2001		GROUP Unknown	
					U.S. PATENT DOCUMENTS			
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EF	AR	S.H. Paek et al., Abstract, <i>Characterization of MIS capacitor of BST thin films deposited on Si by RF magnetron sputtering</i> ,						
		Ferroelectric Thin Films V. Symposium, San Francisco, CA, pp. 33-38 (April 7, 1995).						
EF	AS	N. Takeuchi et al., Abstract, <i>Effect of firing atmosphere on the cubic-hexagonal transition in Ba<sub>0.99</sub>Sr<sub>0.01</sub>TiO<sub>3</sub></i> , 98 NIPPON						
		SERAMIKKUSU KYOKAI GAKUJUTSU RONBUNSHI No. 8, pp. 836-839 (1990).						
EF	AT	H. Yamaguchi, et al., Abstract, <i>Reactive coevaporation synthesis and characterization of SrTiO<sub>3</sub>-BaTiO<sub>3</sub> thin films</i> , IEEE						
		International Symposium on Applications of Ferroelectrics, Greenville, SC, pp. 285-288 (August 2, 1992).						
EXAMINER <i>En. Teller</i>			DATE CONSIDERED <i>12/06/01</i>					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

Form PTO-149 <b>DOPE</b> <b>AUG 29 2001</b> <b>PATENT &amp; TRADEMARK OFFICE</b>				U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1724		SERIAL NO. 09/905,286	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Cem Basceri et al.					
				FILING DATE July 13, 2001		GROUP Unknown			
U.S. PATENT DOCUMENTS									
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
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	AM								
	AN								
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	AP								
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
EF	AR		S. Yamamichi et al., Abstract, <i>Ba + Sr/Ti ratio dependence of the dielectric properties for (Ba<sub>0.5</sub>)Sr<sub>0.5</sub>TiO<sub>3</sub> thin films prepared by ion beam sputtering</i> , 64 APPLIED PHYSICS LETTERS No. 13, pp. 1644-1646 (1994).						
EF	AS		M. Yamamuka et al., Abstract, <i>Thermal-Desorption Spectroscopy of (Ba,Sr)TiO<sub>3</sub> Thin-Films Prepared by Chemical-Vapor-Deposition</i> , 35 JPN. J. OF APPL. PHYS. Pt. 1, No. 2A, pp. 729-735 (1996).						
EF	AT		Arai T., et al.: <i>Preparation of SrTiO<sub>3</sub> Films on 8-Inch Wafers by Chemical Vapor Deposition</i> , Jap. Journal of Applied Physics, Vol. 35, No. 9B, Part 01, 09/01/96, Pgs. 4875-4879						
EXAMINER <i>John G. Miller</i>				DATE CONSIDERED <i>12/06/01</i>					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

Form PTO-109 OCT 2007 AUG 29 2001		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1724		SERIAL NO. 09/905,286	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Cem Basceri et al.			
				FILING DATE July 13, 2001		GROUP Unknown	
U.S. PATENT DOCUMENTS							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EF	AR		Kim, et al.: <i>Structural and Electrical Properties of BaTiO<sub>3</sub> grown on p-InP (100) by low-pressure metalorganic chemical vapor deposition at low temperature</i> , Applied Physics Letters, US, American Institute of Physics Vol. 65, No. 15, 10/10/94, Pgs. 1955-1957.				
	AS						
	AT						
EXAMINER 		DATE CONSIDERED 12/06/01					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							